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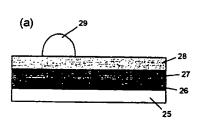
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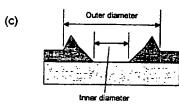
[Continued on next page]

(54) Title: FORMING INTERCONNECTS

tle Park, Cambridge CB3 OAX (GB).



(57) Abstract: A method for forming an electronic device, comprising: forming a first conductive or semiconductive layer; forming a sequence of at least one insulating layer and at least one semiconducting layer over the first conductive or semiconductive layer; locally depositing solvents at a localised region of the insulating layer so as to dissolve the sequence of insulating and semiconducting layers in the region to leave a void extending through the sequence of layers: and depositing conductive or semiconductive material in the void.



ΡVΡ 120 750դm Diameter of Hole (micron 100 Outer diamete 80 25 30 Diameter of Drop (micron)

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patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, Cl, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

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A CLASSIF	ICATION OF SUBJECT MATTER H01L51/40 H01L21/311			
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According to	International Patent Classification (IPC) or to both national classificat	tion and IPC		
B. FIELDS S	SEARCHED currentation searched (classification system followed by classification	n symbols)		
IPC 7	HO1L	•		
Documentati	on searched other than minimum documentation to the extent that su	ich documents are inclu	ded in the fields sea	urched
Electronic da	ta base consulted during the international search (name of data base	e and, where practical,	search terms used)	
INSPEC	, EPO-Internal			
C. DOCUME	NTS CONSIDERED TO BE RELEVANT			
Category *	Citation of document, with indication, where appropriate, of the rele	want passages		Relevant to claim No.
X	WO 99 10939 A (KONINKL PHILIPS EL NV ;PHILIPS AB (SE)) 4 March 1999 (1999-03-04) the whole document	LECTRONICS		44-48
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X	EP 0 933 814 A (IMEC INTER UNI MI ELECTR) 4 August 1999 (1999-08-04 the whole document	ICRO 4)		49
A	US 4 140 572 A (STEIN LEONARD) 20 February 1979 (1979-02-20) the whole document			1,4
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X Furl	ther documents are listed in the continuation of box C.	X Patent family	members are listed	n annex.
"A" docum consi "E" earlier filing "L" docum which citatic "O" docum other	ategories of cited documents: ent defining the general state of the art which is not dered to be of particular relevance document but published on or after the international date ent which may throw doubts on priority claim(s) or is cited to establish the publication date of another or other special reason (as specified) tent reterring to an oral disclosure, use, exhibition or means ent published prior to the international filing date but than the priority date claimed	cited to understar invention "X" document of partic cannot be consid- involve an inventi "Y" document of partic cannot be consid- document is com-	d not in conflict with not the principle or the gred novel or cannot we step when the do utar retevance; the ered to involve an in bined with one or my bination being obvio	the application but every underlying the laimed invention be considered to cument is taken alone laimed invention ventive step when the every such docu- us to a person skilled
1	actual completion of the International search	Date of mailing of	the international sea	urch report
:	19 February 2001	.18.0	5. 01	
Name and	mailing address of the ISA European Patent Office, P.B. 5818 Patentiaan 2 NL - 2280 HV Rijswifk Tel. (+31-70) 340-2040, Tx. 31 651 epo nt, Fax: (+31-70) 340-3018	Authorized officer Königs	tein, C	

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Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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ational application No. PCT/GB 00/04940

Box I Obse	ervations where certain claims were found unsearchable (Continuation of item 1 of first sheet)
This Internation	nal Search Report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:
1. Claim becau	is Nos.: use they relate to subject matter not required to be searched by this Authority, namely:
l =	is Nos.: use they relate to parts of the International Application that do not comply with the prescribed requirements to such stent that no meaningful International Search can be carried out, specifically:
beca	ns Nos.: use they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).
Box II Obs	ervations where unity of Invention is lacking (Continuation of item 2 of first sheet)
This Internation	onal Searching Authority found multiple inventions in this international application, as follows:
sed	e additional sheet
1. As a sear	Il required additional search fees were timely paid by the applicant, this International Search Report covers all chable claims.
2. As a of au	til searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment ny additional fee.
3. As c	only some of the required additional search fees were timety paid by the applicant, this International Search Report ers only those claims for which fees were paid, specifically claims Nos.:
rest	required additional search fees were timely paid by the applicant. Consequently, this International Search Report is tricted to the invention first mentioned in the claims; it is covered by claims Nos.: -38,44-49
Remark on	Protest The additional search fees were accompanied by the applicant's protest. No protest accompanied the payment of additional search fees.

FURTHER INFORMATION CONTINUED FROM PCT/ISA/ 210

This International Searching Authority found multiple (groups of) inventions in this international application, as follows:

1. Claims: 1-38,44-49

Patterning of organic insulating layers by selective etching

The prior Art describes a field effect transistor substantially consisting of organic materials.

The new features mentioned in claims 1-38 are contact holes, made in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

From this we can formulate an objective problem of making contact holes in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

The special technical features, as defined in Rule 13(2) PCT, are contact holes, made in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

2. Claims: 39-43

Selective doping of organic insulating layers

The prior Art describes a field effect transistor substantially consisting of organic materials.

The new features mentioned in claims 1-38 are conductive (interconnection) patterns made by selective doping organic insulating layers to make them conductive. The dopants are applied using an ink-jet printing system.

From this we can formulate an objective problem of making conductive patterns made by selective doping organic insulating layers to make them conductive, applying the dopants are using an ink-jet printing system.

The special technical features, as defined in Rule 13(2) PCT, are conductive (interconnection) patterns made by selective doping organic insulating layers to make them conductive. The dopants are applied using an ink-jet printing system.

autormation on patent family members

tntern-"mail Application No PC1/GB 00/04940

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